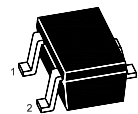
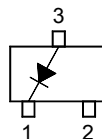


MMBD142W

Silicon Epitaxial Planar Switching Diode

Applications

- for switching circuits



SOT-323 Plastic Package
Marking Code: **D3**

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Forward Current	I_F	100	mA
Peak Forward Current	I_{FM}	225	mA
Non-repetitive Peak Forward Surge Current ($t = 1\text{ s}$)	I_{FSM}	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	1.2	V
Reverse Current at $V_R = 75\text{ V}$	I_R	-	0.1	μA
Reverse Voltage at $I_R = 100\text{ }\mu\text{A}$	V_R	80	-	V
Terminal Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_t	-	15	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $I_{rr} = 0.1 \cdot I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	10	ns

